

Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HBD241C

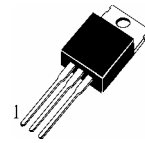
APPLICATIONS

Medium Power Linear And Switching Applicatione.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

T_{stg} —Storage Temperature.....	$-65\sim 150^{\circ}\text{C}$
T_j —Junction Temperature.....	150°C
P_C —Collector Dissipation ($T_c=25^{\circ}\text{C}$)	40W
V_{CER} —Collector-Emitter Voltage.....	115V
V_{CEO} —Collector-Emitter Voltage.....	100V
V_{EBO} —Emitter-Base Voltage.....	5V
I_C —Collector Current (DC)	3A
I_C —Collector Current (Pulse)	5A
I_B —Base Current.....	1A

TO-220



1 — Base, B
2 — Collector, C
3 — Emitter, E

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$BV_{\text{CEO(SUS)}}$	Collector-Emitter Sustaining Voltage	100			V	$I_C=30\text{mA}$, $I_B=0$
I_{CEO}	Collector Cut-off Current			300	nA	$V_{\text{CE}}=60\text{V}$, $I_B=0$
I_{EBO}	Emitter-Base Cutoff Current			1	mA	$V_{\text{EB}}=5\text{V}$, $I_C=0$
I_{CES}	Collector Cutoff Current			200	μA	$V_{\text{CE}}=100\text{V}$, $V_{\text{BE}}=0$
$H_{\text{FE}}(1)$	DC Current Gain	25				$V_{\text{CE}}=4\text{V}$, $I_C=1\text{A}$
$H_{\text{FE}}(2)$		10				$V_{\text{CE}}=4\text{V}$, $I_C=3\text{A}$
$V_{\text{CE(sat)}}$	Collector- Emitter Saturation Voltage			1. 2	V	$I_C=3\text{A}$, $I_B=0.6\text{A}$
$V_{\text{BE(on)}}$	Base- Emitter On Voltage			1. 8	V	$V_{\text{CE}}=4\text{V}$, $I_C=3\text{A}$,